Quick Start Microsystems, LLC
Getting Started Quickly in Microelectronics, Microsystems & Reliability Series

21st Century Semiconductor Technology Handbook

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A fast, easy-to-understand way for people working in the industry to develop an intuitive understanding of:

- *How microelectronic and optoelectronics devices work*
- *How ICs are fabricated*
- *What are the up-to-date challenges that are reshaping deep submicron microelectronics*

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This book is designed to rapidly introduce the basic ideas of microelectronics. As such it contains many simplifying assumptions and omissions. Furthermore, we cannot guarantee the accuracy of everything in this book. Therefore, it should be used for instruction, not to make manufacturing or other similar decisions.

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Table of Contents (Short)

MODULE I. INTRODUCTION
1 Introduction
2 Economics and Industry Structure
3 Overview
MODULE II. SEMICONDUCTORS
1 Intrinsic Semiconductors
2 Extrinsic Semiconductors
3 Currents in Semiconductors
4 pn Junctions
5 Metal/Semiconductor Junctions and Heterojunctions
MODULE III. METAL OXIDE SEMICONDUCTOR
1 MOS Capacitor
2 MOS Transistor
3 Scaling
4 Non-Ideal Effects
MODULE IV. INTEGRATED CIRCUITS
1 Integrated Circuits
2. Packaging
MODULE V. BASIC PROCESSES
1 Starting Material
2 Defect Reduction
3 Lithography
4 Planarization
5 Doping
6 Deposition
7 Etching
MODULE VI. MOS PROCESSING
1 Process Integration
2 Process Flow
MODULE VII. RELIABILITY
1 Yield, Reliability and Quality
MODULE VIII. FUTURE TRENDS
1 Future Trends
2 New Devices
MODULE IX. OPTOELECTRONICS
1 Photo Diodes and Solar Cells
2 LEDs, Laser Diodes and VCSELs

GLOSSARY
APPENDIX I: PHYSICAL CONSTANTS, METRIC PREFIXES & SYMBOLS
APPENDIX II: THE BASIC EQUATIONS OF DEVICE PHYSICS

Table of Contents (Detailed)

MODULE I. INTRODUCTION

I.1. Introduction
- 1. The Silicon Miracle
- 2. A Brief History of Microelectronics
  - 2.1 The Invention of the Transistor
  - 2.2 1950s Laying The Foundation for Integrated Circuits
  - 2.3 The Invention of the Integrated Circuit
  - 2.4 The Foundations of Faster, Better, Cheaper
  - 2.5 The Evolution of Technology
  - 2.6 The Development of the Industry
  - 2.7 Lessons Learned From History
- 3. The Moore's Law Cycle That Has Driven The Industry
  - 3.1 The Start of the Cycle: Investing in the Next Generation.
  - 3.2 The Middle of the Cycle: Faster, Better, Cheaper ICs
  - 3.3 The End of the Cycle: The Economic Payoff
- 4. The Future: A Period of Unprecedented Change
  - 4.1 Future projections
  - 4.2 The Moore's Law Cycle Is Under Attack
  - 4.3 "Rumors of my death have been greatly exaggerated."
  - 4.4 "Decade of Unprecedented Change"
  - 4.5 A Possible Future Scenario
  - 4.6 Microsystems

I.2 Economics and Industry Structure
- 1. Introduction
- 2. Economics 101
- 3. Income: Selling Chips
  - 3.1 Boom and Bust
  - 3.2 Selling Price of ICs
  - 3.3 Time is Money I
- 4. Expenses
  - 4.1The Rising Cost of IC Factories: Moore's 2nd Law
  - 4.2 Time is Money II
  - 4.3The Rising Cost of Problems: Dellin's Law
- 5. Changing Industry Structure
  - 5.1 Fabless Design Houses and (Design-less) Foundries
  - 5.2 Complete Solution Equipment Suppliers
- 6. System on a Chip (SOC)
- 7. Reducing the cost per transistor

I.3. Overview of CMOS
- 1. Introduction
- 2. Semiconductors

3. Semiconductor Devices
    - 3.1 Junctions and Diodes
    - 3.2 The Transistor is a Device to Control Currents
    - 3.3 Review of Electric Circuit Concepts
    - 3.3 Only Two Things™
    - 3.4 MOS Transistor
    - 3.5 Scaling
4. Integrated Circuits
5. Processing
    - 5.1 Processing Hierarchy
    - 5.2 Unit Processes
    - 5.3 Process Modules and Process Integration
    - 5.4 CMOS Technology
6. "The Big Picture"

MODULE II. SEMICONDUCTORS

II.1. Intrinsic Semiconductors

1 Introduction
2. Crystals
3. The Silicon Crystal
4. Conduction and Valence Bands
5. Electrons and Holes in Semiconductors
    - 5.1 Thermal Generation of Electron Hole Pairs
6. Number of Electrons and Holes
7. Location of Electrons and Holes
6. Generation and Recombination

II.2 Extrinsic Semiconductors

1. Extrinsic (Doped) Semiconductors
2. n Type Semiconductor
3. p Type Semiconductor
4. The Electron Hole Product
    - 4.1 The Number of Electrons and Holes in n and p type Semiconductors
5. Compensation and Counter Doping
6. Effect of Temperature on Carrier Concentrations
7. Resistivity
8. Degenerately Doped Semiconductor
9. The Fermi Level

II.3. Currents in Semiconductors

1. Currents
2. Diffusion Currents
3. Drift Currents
4. Mobility

        4. Universal Mobility Curves for Transistors
    5. The Einstein Relationship Between Drift and Diffusion

II.4. pn Junctions

1. Junctions
2. pn Junctions: The Basic Building Block of Semiconductor Devices
3. The Unbiased pn Junction
    - 3.1 Forming the pn Junction
    - 3.2 Features of the pn Junction
    - 3.3 One-sided Junctions
4. The pn Junction with an External Voltage Applied
    - 4.1 Minority Carrier Injection and Extraction
    - 4.2 Junction Switching Speed
    - 4.3 Currents in One-Side Junctions

5. Reverse Bias Leakage Currents
6. Depletion Widths Determine The Minimum Size Of Transistors
7. Junction Breakdown

II.5. Metal/Semiconductor Junctions and Heterojunctions

1. Metals and Semiconductors
2. Work Function
3. The Metal Semiconductor Junction
4. Making Good Electrical Contact to Semiconductors
5. Heterojunctions

<u>MODULE III. METAL OXIDE SEMICONDUCTOR</u>

III.1. MOS Capacitor

1. Introduction
2. MOS Capacitor
3. Threshold Voltage
    - 3.1 Flat Band Voltage
    - 3.2 Adjusting The Threshold Using Ion Implantation
    - 3.3 Temperature Dependence of the Threshold
4. CV Curves

III.2. The Ideal MOS Transistor

1. Introduction
2. The n Channel Transistor Will Be Studied
3. The Transistor’s Geometry
4. The Transistor Has Four Electrical Connections
5. Applying Voltage to the Transistor With No Current Flow
6. Applying Both a Gate & Drain Voltage
7. Linear Current Region of Transistor Action
8. Saturation Current Region of Transistor Operation

9. Using Substrate (Back Gate) Bias To Change Threshold Voltage
10. Subthreshold Currents

III.3. Scaling
1. Introduction
2. Ideal, Constant Field Scaling
3. Real World Scaling
4. Some Things Get Worse With Scaling

III. 4 Non-Ideal Effects
1. Introduction
2. Short Channel Effect
3. Tunneling through the gate oxide
4. Velocity Saturation
5. Electrical Thickness of Gate Insulator

MODULE IV. INTEGRATED CIRCUITS

IV.1 Integrated Circuits
1. Introduction
2. A Simple Model for IC Performance
3. Parasitics
    3.1 Sources of Parasitic Resistance and Capacitance
    3.2 Source and Drain Parasitics
    3.3 Interconnect Parasitics
4. Cross Talk
5. A Simple Model for IC Power
6. Tradeoffs: Power versus Performance
    6.1. The need for tradeoffs

6.2 Power versus performance

IV.2 Packaging
1. Introduction
2. Packaging and Assembly
    2.1 Die Separation
    2.2 Mounting Die
    2.3 Wire Bonding
    2.4 Plastic Encapsulation
    2.5 Ceramic Packages
3. Package Types
4. Flip Chip and Ball Grid Array
5. Multiple Die in a Package

MODULE V. BASIC PROCESSES

V.1 Starting Material

1. Amorphous, Crystalline and Polycrystalline Materials
2. Specifying Crystal Planes and Directions: Miller Indices
3. The Diamond and Quartzite Crystal Structures
4. Surfaces of Crystals
5. Importance of Crystal Orientation
6. Crystal Growing
7. Epitaxial Wafers
8. Silicon on Insulator (SOI)

V.2 Controlling Defects and Contamination

1. Three-Part Strategy
2. Reducing particles and contaminants
3. Cleaning
4. Gettering

V.3 Photolithography: Patterning Features

1. Introduction
2. Masks
3. Process Flow
4. Photoresist (PR)
5. Resolution and Depth of Focus
6. Exposure Systems
7. Sub-wavelength Lithography

V.4 Planarization and Chemical Mechanical Polishing (CMP)

1. Planarization: Removing Unwanted Topography
2. Reflowing glass
3. Etch back
4. Chemical Mechanical Polishing (CMP)
    - 4.1 CMP Challenges
    - 4.2 Post CMP Cleaning

V.5 Doping (Implant and Diffusion)

1. Doping
2. Ion Implantation
    - 2.1 Range and Straggle
    - 2.2 Channeling
    - 2.3 Implant Damage and Annealing
3. Diffusion
    - 3.1 Qualitative Description of Diffusion
    - 3.2 Simple Analytical Solutions

V.6 Thin Films: Oxidation and Deposition

1. Deposition: Adding Thin Films
2. Thermal Growth
    - 2.1 Thermal Oxidation
    - 2.2 Using Silicon Nitride as a Thermal Oxidation Mask
    - 2.3 Segregation of Dopants During Oxidation
    - 2.4 Silicides
3. Chemical Vapor Deposition (CVD)
    - 3.1 Plasma Enhanced CVD (PECVD)
    - 3.2 High Density Plasma CVD
    - 3.3 Atomic Layer Deposition
    - 3.4 Epitomical Si
    - 3.5 Polysilicon
    - 3.6 CVD Oxides
    - 3.7 CVD Silicon Nitride
    - 3.8 CVD Tungsten (W)
4. Physical Vapor Deposition (PVD)
5. Electroplating
6. Spin on Films

V.7 Etching

1. Etching
    - 1.1 Isotropic vs. Anisotropic Etching
    - 1.2 Etch Selectivity
    - 1.3 Using a Hard Mask
2. Wet Etching
3. Plasmas
4. Dry Etching
    - 4.1 Etching High Aspect Ratio Vias: Sidewall Polymers
    - 4.2 Macro-Loading and Micro-Loading
    - 4.3 Etching Oxides
    - 4.4 Etching Polysilicon
    - 4.5 Etching Al
    - 4.6 Plasma Charging Damage
5. CMP Etching in Damascene Process

MODULE VI. MOS PROCESSING

VI.1. CMOS Process Integration

1. Introduction
2. Potential Parasitic Leakage Current Paths
3. Wells
    - 3.1 Single Well vs. Dual Well (Twin Tub)
    - 3.2 Forming the Well by Drive In or By High Energy Implant
4. Isolation
    - 4.1 Guard Bands

- 4.2 LOCOS (Local Oxidation of Silicon)
- 4.3 Shallow Trench Isolation (STI)

5. Gate Stack
   - 5.1 P+ vs. N+ Polysilicon Gates for PMOS
6. Source and Drain
7. Electrical Contact to Silicon
8. Multilevel Metalization
   - 8.1 Aluminum and Copper
   - 8.2 Dielectric Between Metal Lines
9. Passivation and Bondpads
10. Process Integration

VI.2. CMOS Technology Process Flow

1. Introduction
2. CMOS Process Flow
3. Front End of Line (FEOL)
   - 3.1 Starting Wafers
   - 3.2 Mask 1: Shallow Trench Isolation (STI)
   - 3.3 Mask 2: P Wells and Mask 3: N Wells (“Twin Well/Twin Tub”)
   - 3.4 Gate Insulator
   - 3.5 Mask 4: Polysilicon Gate
   - 3.6 Mask 5: n Channel Shallow Source/Drain Extensions
   - 3.7 n Channel HALO (or Pocket) Implants
   - 3.7 Mask 6: n Channel Shallow Source/Drain Extensions
   - 3.8 n Channel HALO (or Pocket) Implants
   - 3.9 Gate Sidewall Spacer
   - 3.10 Masks 7 and 8: Deep Source and Drain Regions
   - 3.11 Comparison of Epi and SOI Wafers After FEOL
4. Back End of Line (BEOL)
   - 4.1 SALICIDE (Self Aligned Silicide)
   - 4.2 Mask 9: Interlevel Dielectric and Contact Cut
   - 4.3 Contact Metalization
   - 4.4 Mask 10: Metal 1 (M1)
   - 4.5 Masks 11 and 12: Metal 1/Metal 2 Via and Metal 2
   - 4.6 Terminology
   - 4.7 Masks 13-20: Rest of Vias and Metal Levels
   - 4.8 Mask 20: Bond Pad and Passivation
5. Copper Metalization
6. Bond Pads and Passivation

MODULE VII. RELIABILITY

VII.1 Reliability, Yield & Quality

1 The Most Important Thing

2 Yield

3 Reliability

4 IC Failure Modes
   4.1 Dielectric Breakdown
   4.2 Hot Carrier Degradation
   4.3 Electromigration
   4.4 Stress Voiding
5. Quality

MODULE VIII. FUTURE TRENDS

VIII.1. Future Challenges and Potential Solutions

1. Introduction
2. Technical Challenges
   2.1 Device Physics Challenges
   2.2 Processing Challenges
3. New Materials
   3.1 Cu Interconnect
   3.2 Low k Interlevel Dielectrics
   3.3 High k gate insulators
   3.4 Strained Silicon
4. New Devices
5. Des1gn Challenges
6. Reliability Challenges
7. Economic Challenges
8. Timetable for Changes: International Technology Roadmap for Semiconductors (ITRS)

VIII.2 New Devices

1. Introduction
2. Multiple Threshold Voltages
3. Silicon on Insulator (SOI) Transistors
   3.1 Partially Depleted vs. Fully Depleted
   3.2 Partially Depleted SOI
   3.3 Fully Depleted SOI
4. Multi-gate MOS Transistors
5. Novel transistors

MODULE IX. OPTOELECTRONICS

IX.1 Photo Diodes & Solar Cells

1. Introduction
2. Light
3. Direct and Indirect Bandgap Semiconductors
4. Light Absorption

4.1 Light Absorption in Direct Bandgap Semiconductors
4.2 Light Absorption in Indirect Bandgap Semiconductors
4.3 High Energy Photons are Less Efficient
5. Photodiode
5.1 Spectral Response
6. Photovoltaics
6.1 Solar Cells

IX.2 LEDs, Laser Diodes and VCSELs
1. Introduction
2. Spontaneous Emission
3. Stimulated Emission
4. Forward-Biased Diode as a Light Emitter
4.1 Double Heterostructure
5. Light Emitting Diode
6. Laser Diode
7. VCSEL
8. Comparison of LED, Laser Diode and VCSEL

GLOSSARY

APPENDIX I: PHYSICAL CONSTANTS, METRIC PREFIXES & SYMBOLS

APPENDIX II: THE BASIC EQUATIONS OF DEVICE PHYSICS

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